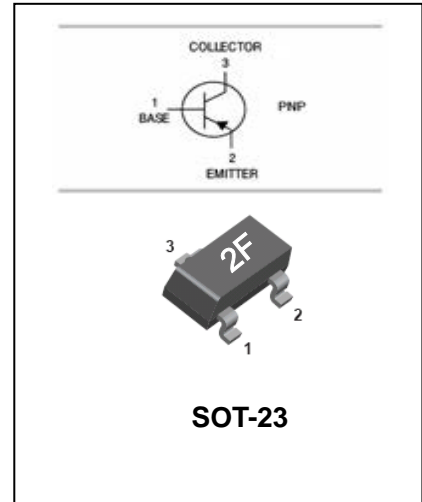


FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available MMBT2222A.
- Ideal for medium power amplification and switching.
- MSL 1

APPLICATIONS

- This device is designed as a general purpose amplifier and switching.
- The useful dynamic range extends to 600mA as a switch and to 100MHz as a amplifier.



MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-600	mA
P _D	Total Device Dissipation	300	mW
R _{θJA}	Thermal Resistance Junction to Ambient	417	°C/W
R _{θJC}	Thermal Resistance Junction to Case	250	°C/W
T _J , T _{STG}	Junction and Storage Temperature	-55 to +150	°C/W

ESD RATING

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A$ $I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA$ $I_B=0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A$ $I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V$ $I_E=0$ $V_{CB}=-50V$ $I_E=0$ $T_A=125^\circ C$		-10 -10	nA μA
Collector cut-off current	I_{CEX}	$V_{CE}=-30V$, $V_{BE(OFF)}=-0.5V$		-50	nA
Base cut-off current	I_{BL}	$V_{CE}=-30V$, $V_{BE(OFF)}=-0.5V$		-50	nA
DC current gain	h_{FE}	$V_{CE}=-10V$ $I_C=-100\mu A$ $V_{CE}=-10V$ $I_C=-1mA$ $V_{CE}=-10V$ $I_C=-10mA$ $V_{CE}=-10V$ $I_C=-150mA$ $V_{CE}=-10V$ $I_C=-500mA$	75 100 100 100 50	- - - 300 -	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150mA$ $I_B=-15mA$ $I_C=-500mA$ $I_B=-50mA$		-0.4 -1.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-150mA$ $I_B=-15mA$ $I_C=-500mA$ $I_B=-50mA$		-1.3 -2.6	V
Transition frequency	f_T	$V_{CE}=-20V$ $I_C=-50mA$ $f=100MHz$	200		MHz
Output Capacitance	C_{obo}	$V_{CB}=-10V$ $f=100kHz$ $I_E=0$	-	8.0	pF
Input Capacitance	C_{ibo}	$V_{EB}=-2V$ $f=100kHz$ $I_C=0$	-	30	pF
Delay time	t_d	$V_{CE}=-30V$, $I_C=-150mA$, $I_{B1}=-15mA$		10	ns
Rise time	t_r			40	ns
Storage time	t_s	$V_{CE}=-6V$, $I_C=-150mA$		225	ns
Fall time	t_f	$I_{B1}=-I_{B2}=-15mA$		60	ns

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

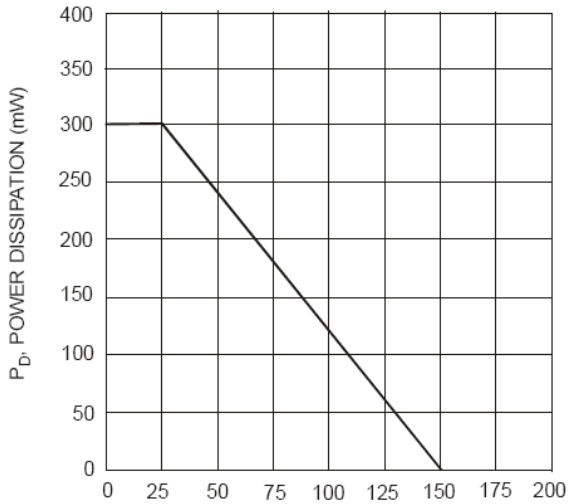


Fig. 1, Max Power Dissipation vs Ambient Temperature

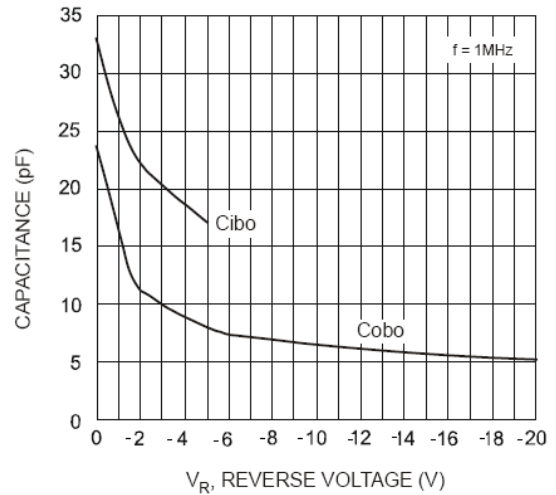


Fig. 2, Typical Capacitance Characteristics

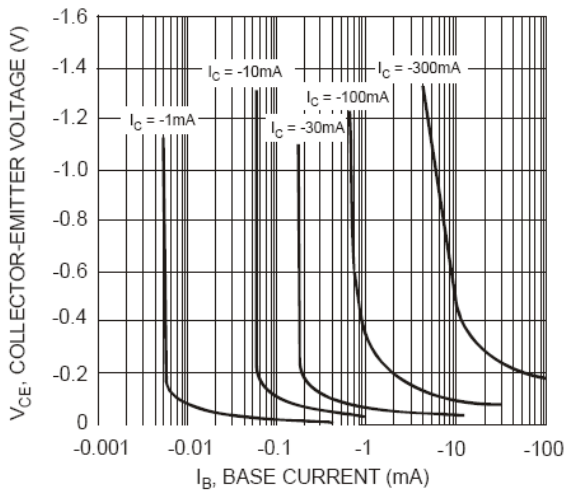


Fig. 3, Typical Collector Saturation Region

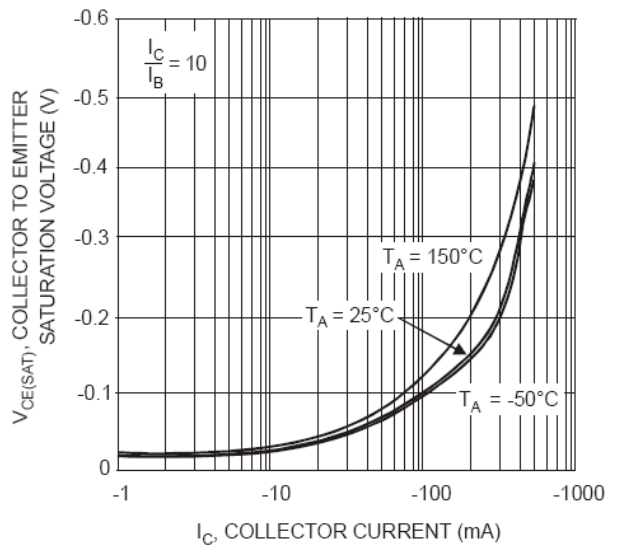


Fig. 4, Collector-Emitter Saturation Voltage vs. Collector Current

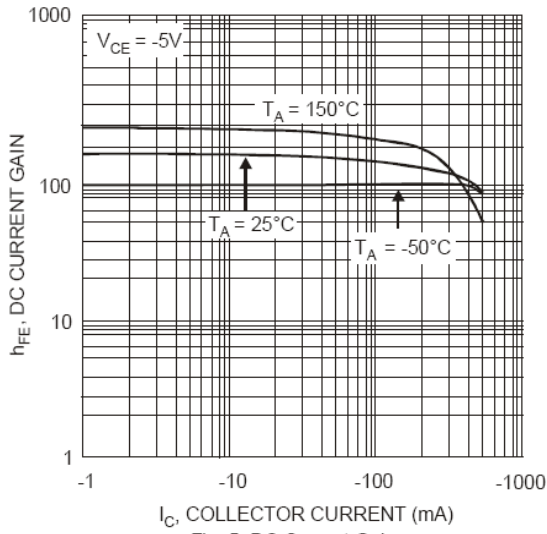


Fig. 5, DC Current Gain vs Collector Current

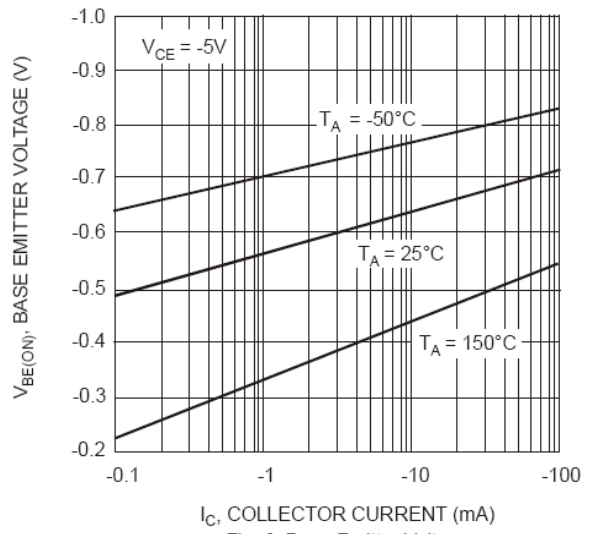


Fig. 6, Base-Emitter Voltage vs. Collector Current

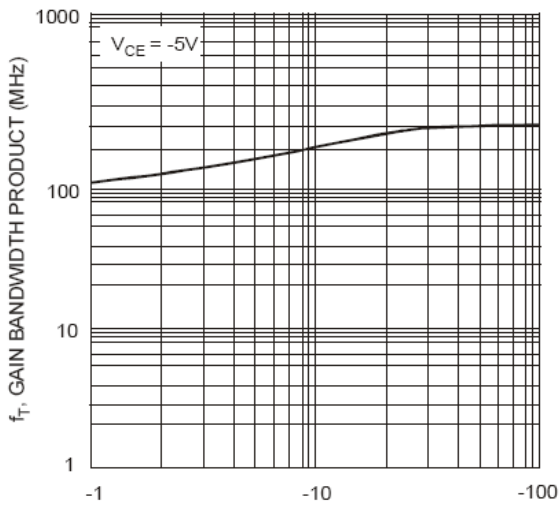
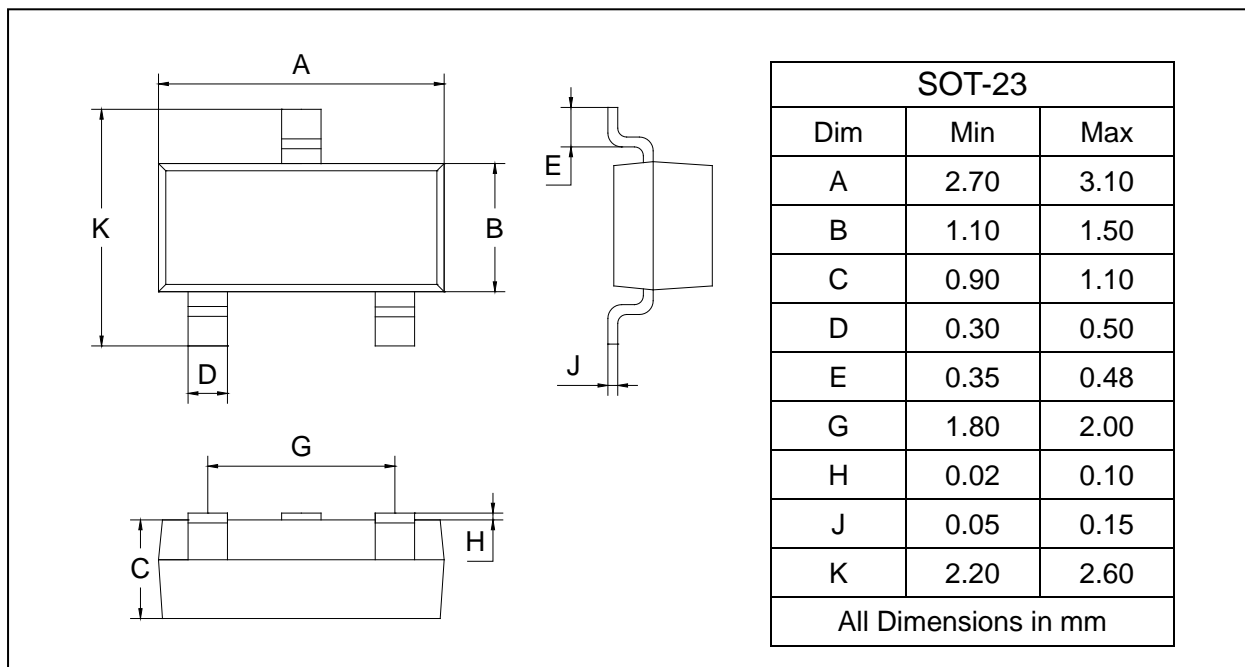


Fig. 7, Gain Bandwidth Product vs. Collector Current

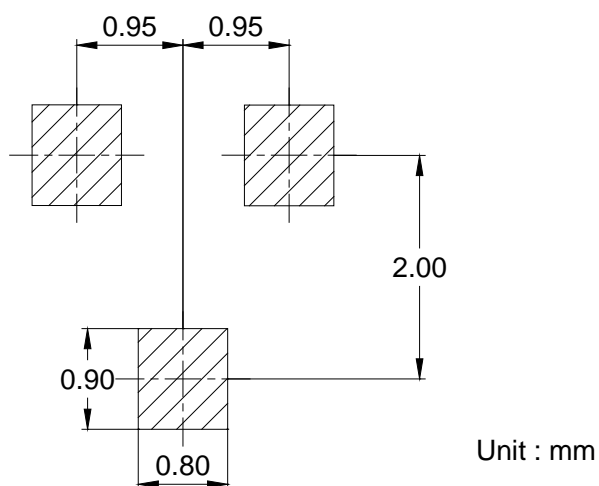
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MMBT2907A	SOT-23	3000 pcs / Tape & Reel